

FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 500466.02	APPLICATION NO. 09/994,511
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Kie Y Ahn; Leonard Forbes	
		FILING DATE November 26, 2001	GROUP ART UNIT 2879

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
K/JN	AA	3,665,241	05/23/72	Spindt et al.	313	351	
K/JN	AB	3,755,704	08/28/73	Spindt et al.	313	309	
K/JN	AC	3,812,559	05/28/74	Spindt et al.	29	25	
K/JN	AD	4,266,233	05/05/81	Bertotti et al.	357	22	
K/JN	AE	5,142,184	8/25/92	Kane	313	309	
K/JN	AF	5,194,780	3/16/93	Meyer	315	169.3	
K/JN	AG	5,229,331	07/20/93	Doan et al.	437	228	
K/JN	AH	5,259,799	11/09/93	Doan et al.	445	24	
K/JN	AI	5,358,908	10/25/94	Reinberg et al.	437	228	
K/JN	AJ	5,372,973	12/13/94	Doan et al.	437	228	
K/JN	AK	5,483,067	01/09/96	Fujii et al.	250	338.3	
K/JN	AL	5,578,896	11/26/96	Huang	313	309	
K/JN	AM	5,585,301	12/17/96	Lee et al.	437	60	
K/JN	AN	5,597,444	01/28/97	Gilton	156	643	
K/JN	AO	5,653,619	08/05/97	Cloud et al.	445	24	
K/JN	AP	5,853,492	12/29/98	Cathey et al.	134	3	
K/JN	AQ	5,712,534	1/27/98	Lee et al.	315	169.3	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AR							

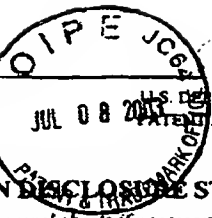
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

K/JN	AS	Anderson, R.C. et al., "Porous Polycrystalline Silicon: A New Material for MEMS," <i>Journal of Microelectromechanical Systems</i> 3(1):10-18, 1994
K/JN	AT	Boswell, E.C. et al., "Polycrystalline Silicon Field Emitters," 8 th International Vacuum Microelectronics Conference Technical Digest, pp. 181-186, 1996

EXAMINER KENNETH J. RAMSEY PRIMARY EXAMINER	DATE CONSIDERED 10/24/03
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* EXAMINER: Initial if reference considered, whether or not criteria is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant(s).

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OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)					
KJA	BA	Boswell, E.C. et al., "Polycrystalline silicon field emitters," <i>J Vac Sci Technol. B</i> 14(3):1910-1913, 1996			
KJA	BB	Huang, W.N. et al., "Photoluminescence in porous sputtered polysilicon films formed by chemical etching," <i>Semicond. Sci. Technol.</i> 12:228-233, 1997			
KJA	BC	Huang, W.N. et al., "Properties of chemically etched porous polycrystalline silicon deposited by r.f. sputtering," <i>IEEE Hong Kong Electron Devices Meeting</i> , pp. 21-24, 1996			
KJA	BD	Huq, S.E. et al., "Comparative study of gated single crystal silicon and polysilicon field emitters," <i>J. Vac. Sci. Technol. B</i> 15(6):2855-2858, 1997			
KJA	BE	Huq, S.E. et al., "Fabrication of Gated Polycrystalline Silicon Field Emitters," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 367-370, 1996			
KJA	BF	Kim, I.H. et al., "Metal FEAs on Double Layer Structure of Polycrystalline Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 423-426, 1996			
KJA	BG	Kim, I.H. et al., "Fabrication of metal field emitter arrays on polycrystalline silicon," <i>J. Vac. Sci. Technol. B</i> 15(2):468-471, 1997			
KJA	BH	Ku, T.K. et al., "Enhanced Electron Emission from Phosphorus-Doped Diamond-Clad Silicon Field Emitter Arrays," <i>IEEE Electron Device Letters</i> 17(5):208-210, 1996			
KJA	BI	Lacher, F. et al., "Electron field emission from thin fine-grained CVD diamond films," <i>Diamond and Related Materials</i> 6:1111-1116, 1997			
KJA	BJ	Lazarouk, S. et al., "Electrical characterization of visible emitting electroluminescent Schottky diodes based on n-type porous silicon and on highly doped n-type porous polysilicon," <i>Journal of Non-Crystalline Solids</i> 198-200:973-976, 1996			
KJA	BK	Lee, J.H. et al., "A New Fabrication Method of Silicon Field Emitter Array with Local Oxidation of Polysilicon and Chemical-Mechanical-Polishing," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 415-418, 1996			
KJA	BL	Lee, K.R. et al., "Field emission behavior of (nitrogen incorporated) diamond-like carbon films," <i>Thin Solid Films</i> 290-291:171-175, 1996			
KJA	BM	Litovchenko, V.G. et al., "Emission Properties of the Silicon Cathodes Coated with Doped Diamond-Like Carbon Films," <i>IEEE International Conf. On Plasma Science</i> , p. 308, Abstract 7A02, 1997			
KJA	BN	Pullen, S.E. et al., "Enhanced Field Emission from Polysilicon Emitters Using Porous Silicon," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 211-214, 1996			
KJA	BO	Uh, H.S. et al., "Enhanced Electron Emission and Its Stability from Gated Mo-polycide Field Emitters," <i>IEEE</i> , pp. 713-716, 1997			
KJA	BP	Uh, H.S. et al., "Fabrication and Characterization of Gated n+ Polycrystalline Silicon Field Emitter Arrays," 9 th International Vacuum Microelectronics Conference, St. Petersburg, pp. 419-422, 1996			
KJA	BQ	Uh, H.S., "Process design and emission properties of gated n+ polycrystalline silicon field emitter arrays for flat-panel display applications," <i>J. Vac. Sci. Technol. B</i> 15(2):472-476, 1997			
KJA	BR	Vaudaine, P. and Meycr, R., "Microtips Fluorescent Display," technical digest of IFDM 91, pp. 197-200, 1991			
EXAMINER		KENNETH J. RAMSEY PRIMARY EXAMINER		DATE CONSIDERED 10/23/03	
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APPLICANT(S)

Kie Y. Ahn and Leonard Forbes

FILING DATE

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GROUP ART UNIT

2879

U.S. PATENT DOCUMENTS

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KJR	AA	US 6,277,765 B1	08/21/01	Cheng et al.	438	773	
KJR	AB	US 6,333,215 B1	12/25/01	Matsuda et al.	438	149	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						

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							YES	NO
	AK							
	AL							
	AM							
	AN							
	AO							

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AP	
	AQ	

EXAMINER

Kenneth Ramsey

DATE CONSIDERED

10/23/03

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